

isc Silicon NPN Power Transistor

2SC4138

DESCRIPTION

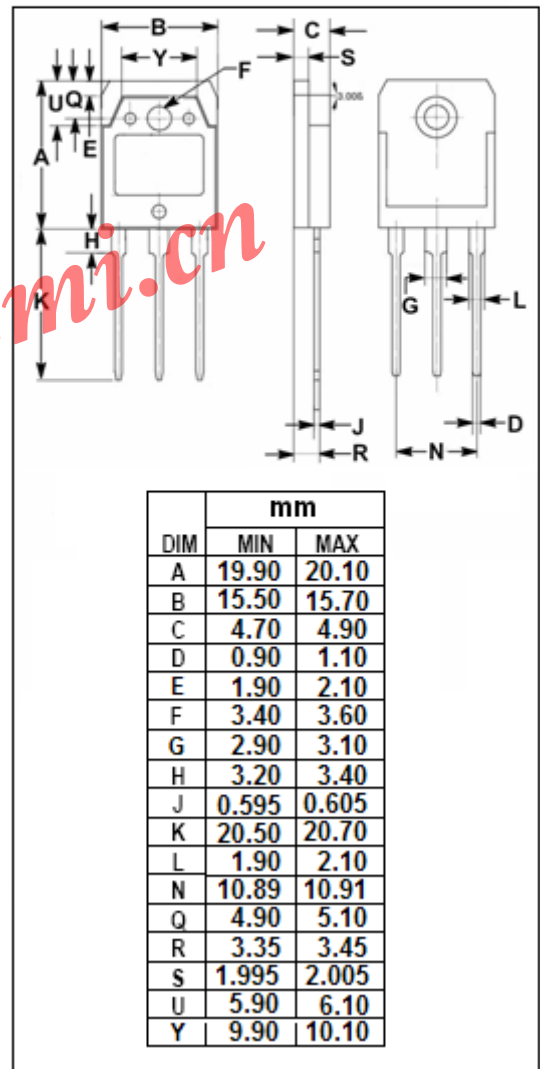
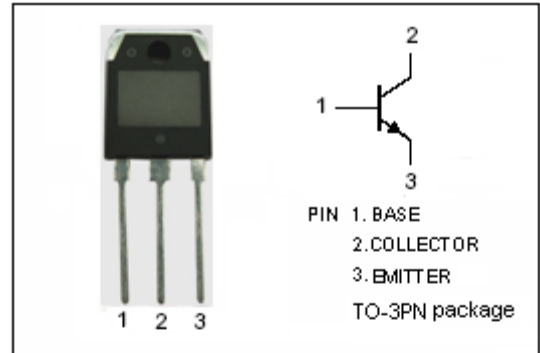
- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed
- High Reliability

APPLICATIONS

- Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	500	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base voltage	10	V
$I_C$	Collector Current-Continuous	10	A
$I_{CM}$	Collector Current-Peak	20	A
$I_B$	Base Current-Continuous	4	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=25\text{mA}; I_B=0$	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.2\text{A}$			1.3	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=10\text{V}; I_C=0$			0.1	mA
$h_{FE}$	DC Current Gain	$I_C=6\text{A}; V_{CE}=4\text{V}$	10		30	
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		85		pF
$f_T$	Current-Gain—Bandwidth Product	$I_E=-0.7\text{A}; V_{CE}=12\text{V}$		10		MHz

## Switching Times

$t_{on}$	Turn-on Time	$I_C=6\text{A}, I_{B1}=0.6\text{A}; I_{B2}=-1.2\text{A}$ $R_L=33.3\Omega; V_{CC}=200\text{V}$			1.0	$\mu\text{s}$
$t_{stg}$	Storage Time				3.0	$\mu\text{s}$
$t_f$	Fall Time				0.5	$\mu\text{s}$